GPT09N50 GPT09N50D

POWER FIELD EFFECT TRANSISTOR

GENERAL DESCRIPTION

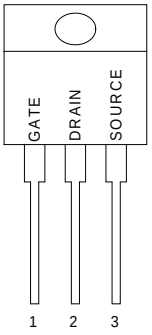
This high voltage MOSFET uses an advanced termination scheme to provide enhanced voltage-blocking capability without degrading performance over time. In addition, this advanced MOSFET is designed to withstand high energy in avalanche and commutation modes. The new energy efficient design also offers a drain-to-source diode with a fast recovery time. Designed for high voltage, high speed switching applications in power supplies, converters and PWM motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer additional and safety margin against unexpected voltage transients.

FEATURES

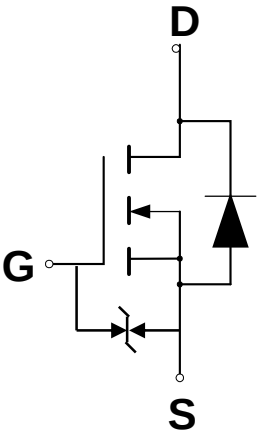
- Robust High Voltage Termination
- Avalanche Energy Specified
- Source-to-Drain Diode Recovery Time Comparable to a Discrete Fast Recovery Diode
- Diode is Characterized for Use in Bridge Circuits
- I_{DSS} and V_{DS}(on) Specified at Elevated Temperature

PIN CONFIGURATION

TO-220F/TO220
Top View



SYMBOL



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain to Current — Continuous	I_D	8.5	A
— Pulsed	I_{DM}	25.5	
Gate-to-Source Voltage — Continue	V_{GS}	±30	V
Total Power Dissipation (TO220)	P_D	140	W
(TO220F)		42	W/℃
Derate above 25℃ (TO220)		1	
(TO220F)		0.32	
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	℃
Single Pulse Drain-to-Source Avalanche Energy — T_J = 25℃ (V_{DD} = 100V, V_{GS} = 10V, I_L = 7A, L = 10mH, R_G = 25Ω)	E_{AS}	245	mJ
Thermal Resistance — Junction to Case (TO220)	θ_{JC}	0.92	℃/W
(TO220F)		4	
— Junction to Ambient	θ_{JA}	62.5	
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T_L	260	℃
ESD SENSITIVITY — HBM, C=100pF, R=1.5kΩ	Vesd	2000	V

ORDERING INFORMATION

Part Number	Package
GPT09N50DGN220FP*	TO-220F
GPT09N50GN220FP*	TO-220F
GPT09N50GN220*	TO-220

***Note:** G : Suffix for PB Free Product

ELECTRICAL CHARACTERISTICS

Unless otherwise specified, T_J = 25℃.

			GPT09N50			
Characteristic		**Symbol**	**Min**	**Typ**	**Max**	**Units**
Drain-Source Breakdown Voltage (V_{GS} = 0 V, I_D = 250 μA)		$V_{(BR)DSS}$	500			V
Drain-Source Leakage Current (V_{DS} = 500 V, V_{GS} = 0 V)		I_{DSS}			1	μA
Gate-Source Leakage Current-Forward (V_{gsf} = 30 V, V_{DS} = 0 V)		I_{GSSF}			100	nA
Gate-Source Leakage Current-Reverse (V_{gsr} = -30 V, V_{DS} = 0 V)		I_{GSSR}			100	nA
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 250 μA)		$V_{GS(th)}$	3		5	V
Static Drain-Source On-Resistance (V_{GS} = 10 V, I_D = 4.5A) *		$R_{DS(on)}$			0.8	Ω
Forward Transconductance (V_{DS} = 50 V, I_D = 4.5A) *		g_{FS}		7		S
Input Capacitance	(V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz)	C_{iss}		983.8		pF
Output Capacitance		C_{oss}		107.4		pF
Reverse Transfer Capacitance		C_{rss}		6.24		pF
Turn-On Delay Time	(V_{DD} = 250 V, I_D = 9 A, R_D = 17Ω, R_G = 6.2Ω) *	$t_{d(on)}$		19.7		ns
Rise Time		t_r		27.2		ns
Turn-Off Delay Time		$t_{d(off)}$		37.6		ns
Fall Time		t_f		22.7		ns
Total Gate Charge	(V_{DS} = 400 V, I_D = 9 A, V_{GS} = 10 V)*	Q_g		22.4		nC
Gate-Source Charge		Q_{gs}		5.17		nC
Gate-Drain Charge		Q_{gd}		9.86		nC
SOURCE-DRAIN DIODE CHARACTERISTICS						
Forward On-Voltage(1)	(I_S =9 A, V_{GS} = 0 V, d_{IS}/d_t = 100A/μs)	V_{SD}			1.5	V
Forward Turn-On Time		t_{on}		**		ns
Reverse Recovery Time		t_{rr}		325.3		ns

* Pulse Test: Pulse Width ≦300μs, Duty Cycle ≦2%

** Negligible, Dominated by circuit inductance

TYPICAL ELECTRICAL CHARACTERISTICS

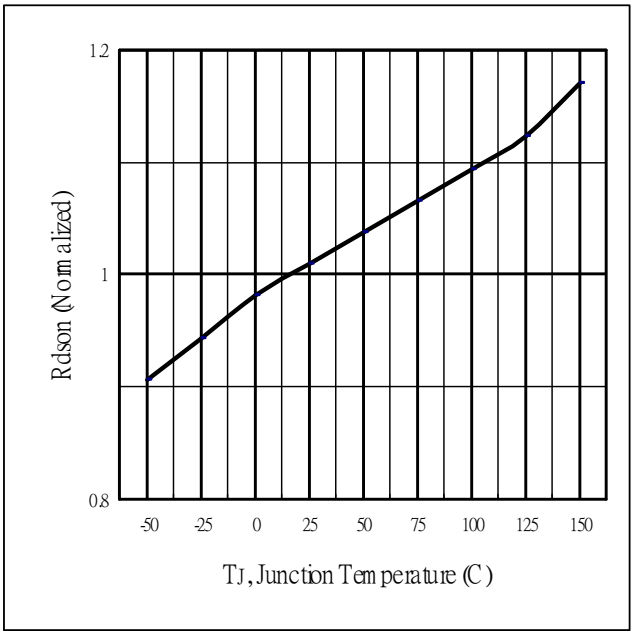


Fig 1. On-Resistance Variation with vs. Temperature

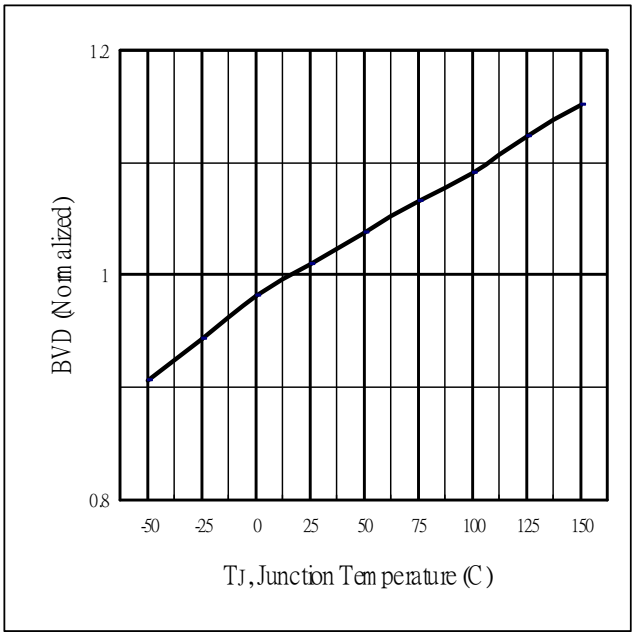


Fig.2 Breakdown Voltage Variation vs. Temperature

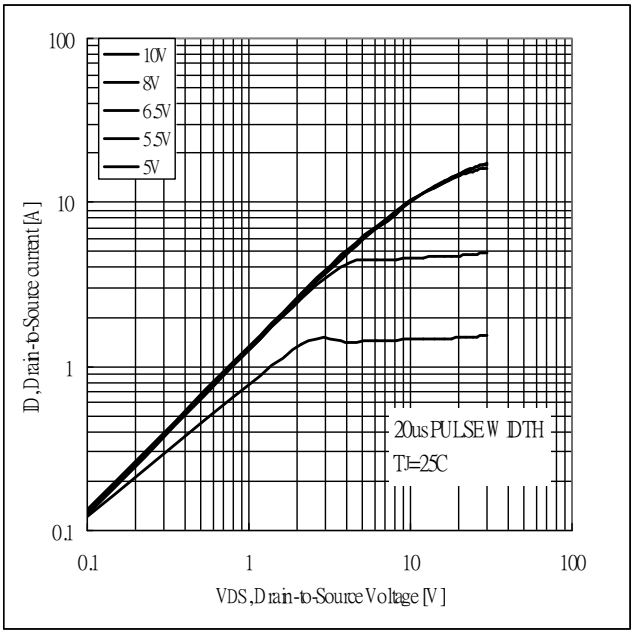


Fig 3. Typical Output Characteristics

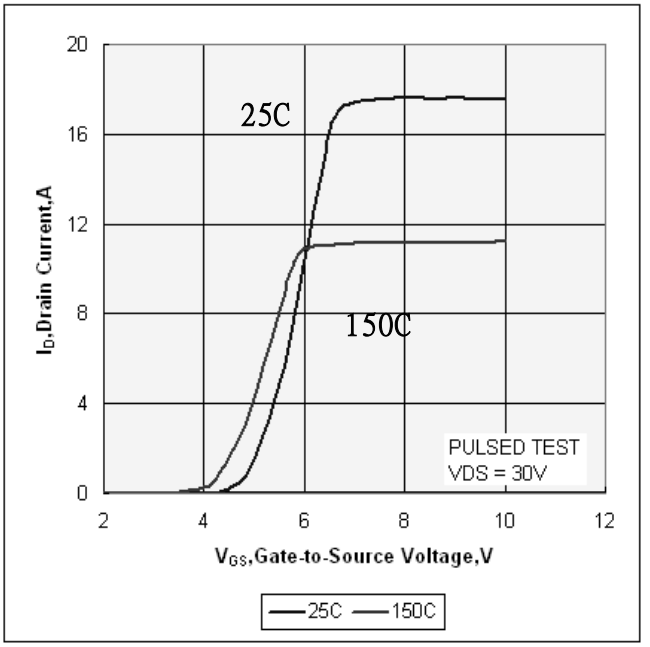


Fig 4. Typical Transfer Characteristics

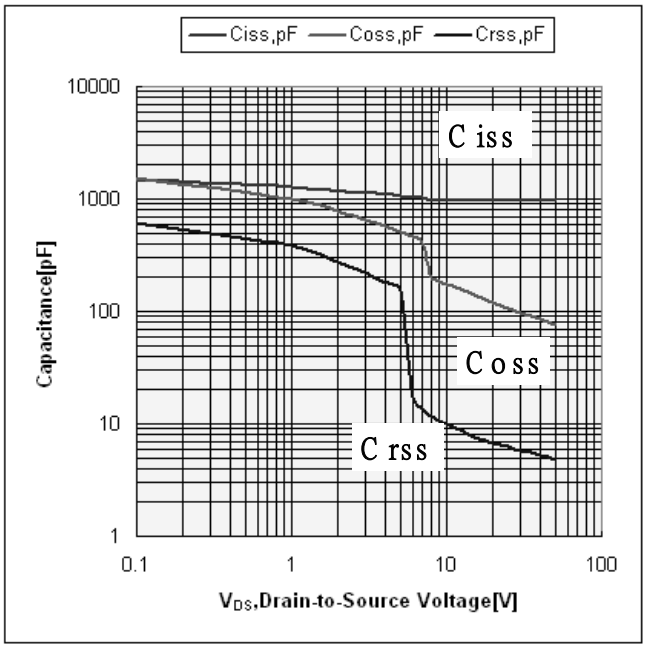


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

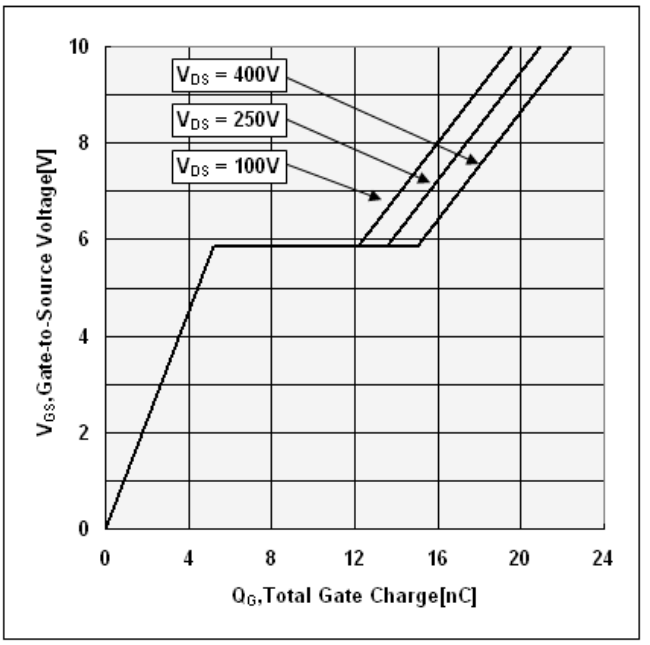
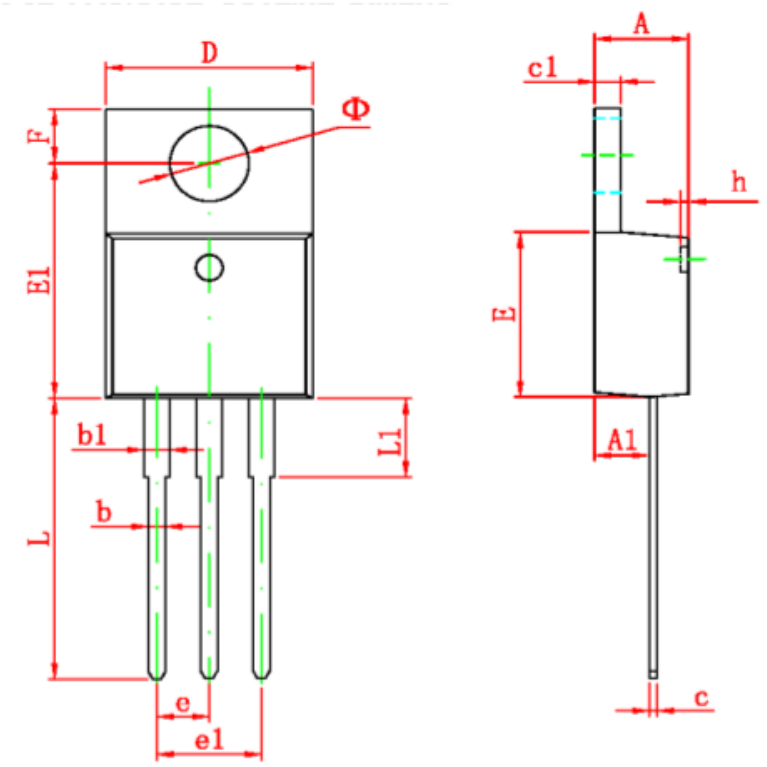


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

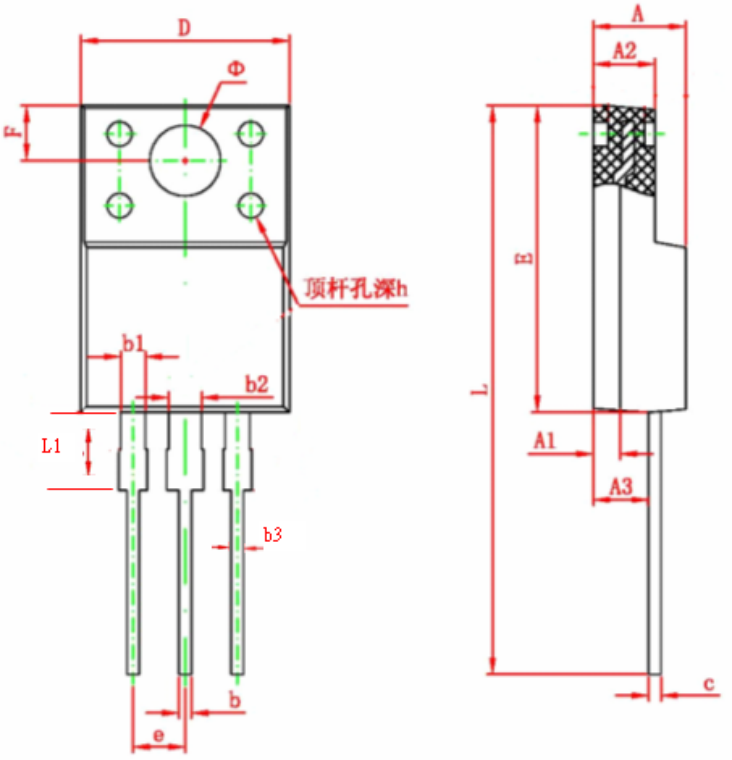
PACKAGE DIMENSION

TO-220



Symbol	Dimensions In Millimeters	
	Min.	Max
A	4.40	4.80
A1	2.10	2.84
b	0.71	0.91
b1	1.17	1.37
c	0.30	0.60
c1	1.17	1.47
D	9.40	10.60
E	8.40	9.60
e	2.54 TYP.	
e1	4.90	5.60
F	3.00 REF.	
Φ	3.50 REF.	
h	0.00	0.30
L	12.50	14.00
L1	3.50	4.00

TO-220F



Symbol	Dimensions In Millimeters	
	Min.	Max
A	3.80	4.70
A1	1.3 REF.	
A2	2.20	3.20
A3	2.10	3.20
b	0.30	0.95
b1	1.00	1.75
b2	1.00	1.75
b3	0.50	0.80
c	0.30	0.90
D	9.90	10.40
E	14.60	16.20
e	2.54 TYP.	
F	3.00 REF.	
Φ	3.50 REF.	
h	0.00	0.30
L	28.00	30.00
L1	3.20	3.55

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